



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} Max	I _D Max T _A = +25°C
	12mΩ @ V _{GS} = -10V	-10.5A
-30V	21mΩ @ V _{GS} = -4.5V	-8.0A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- · ESD Protected Gate
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications Mechanical Data

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

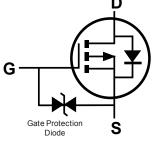
- Backlighting
- Power Management Functions
- DC-DC Converters

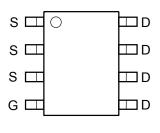
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish Matte Tin Annealed Over Copper Lead Frame.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.074 grams (Approximate)





Top View





Internal Schematic

Top View Pin Configuration

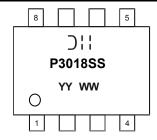
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMP3018SSS-13	SO-8	2,500/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



);; = Manufacturer's Marking
P3018SS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 21 = 2021)
WW = Week (01 to 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-10.5 -8.5	Α
Continuous Drain Current (Note 6) $V_{GS} = -10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +70^{\circ}C$		I _D	-25 -20	А	
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-20	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-90	Α
Avalanche Current (Note 7) L = 1mH			I _{AS}	-14	Α
Avalanche Energy (Note 7) L = 1mH			E _{AS}	104	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	1.2	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		$R_{\theta JA}$	101	°C/W
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		P _D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		R _{0JA}	73	°C/W
Total Power Dissipation (Note 6)	P _D	10	W	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	12.5	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

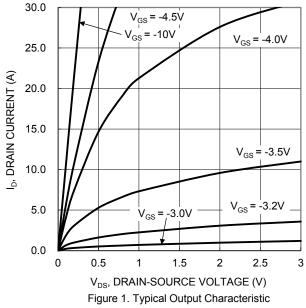
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	1	٧	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)						_	
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	8.7	12	m O	$V_{GS} = -10V, I_D = -11.5A$	
Static Drain-Source On-Resistance	R _{DS(on)}	_	14.5	21	mΩ	$V_{GS} = -4.5V$, $I_{D} = -8.5A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	2,147	_	pF	151/1/ 01/	
Output Capacitance	Coss	_	407		pF	$V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	358	_	pF	I = 1.0WHZ	
Gate Resistance	R_g	_	24	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Q_g	_	28	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	51	_	nC	V 45V 1 44.5A	
Gate-Source Charge	Q_{gs}	_	6.6	_	nC	V_{DS} = -15V, I_{D} = -11.5A	
Gate-Drain Charge	Q_{gd}	_	15	_	nC		
Turn-On Delay Time	t _{D(on)}	_	7.8	_	ns		
Turn-On Rise Time	t _R	_	19.9	_	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(off)}	_	57.5	_	ns	$R_G = 6\Omega$, $I_D = -11.5A$	
Turn-Off Fall Time	t _F	_	42.8	_	ns		
Reverse Recovery Time	t _{RR}	_	21.5	_	ns		
Reverse Recovery Charge	Q_{RR}	_	11.6	_	nC	I _S = -11.5A, dl/dt = 100A/μs	

Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.





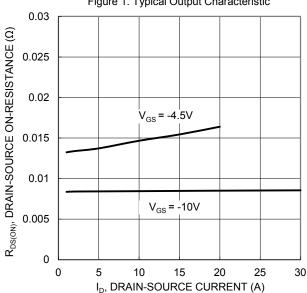


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

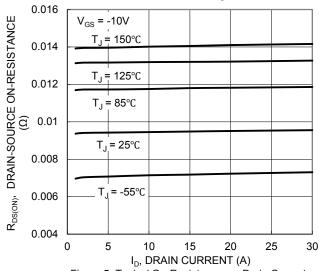


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

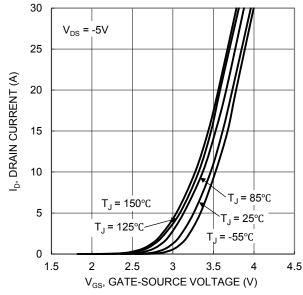


Figure 2. Typical Transfer Characteristic

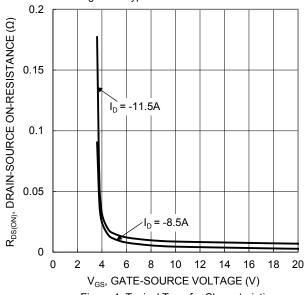


Figure 4. Typical Transfer Characteristic

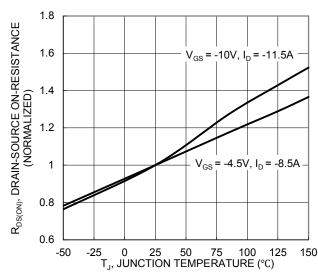


Figure 6. On-Resistance Variation with Junction Temperature



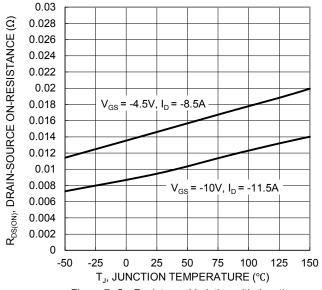


Figure 7. On-Resistance Variation with Junction Temperature

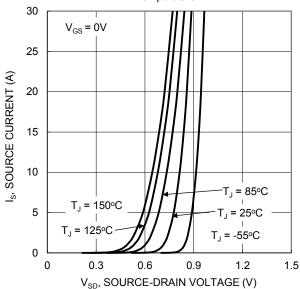
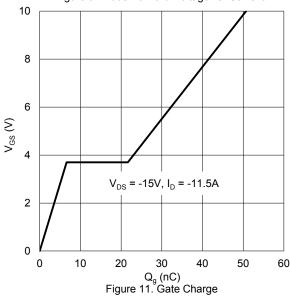


Figure 9. Diode Forward Voltage vs. Current



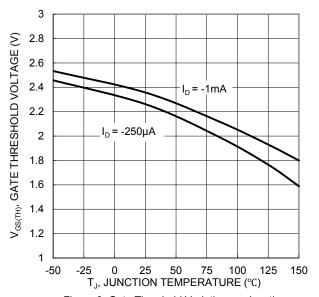


Figure 8. Gate Threshold Variation vs. Junction Temperature

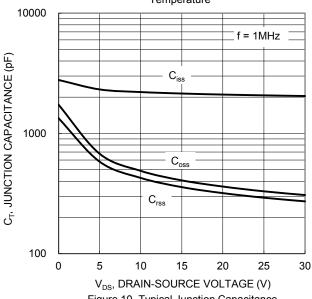
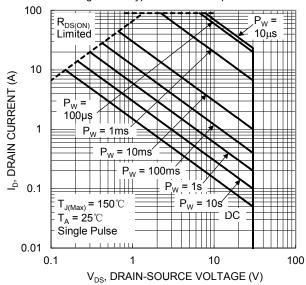


Figure 10. Typical Junction Capacitance





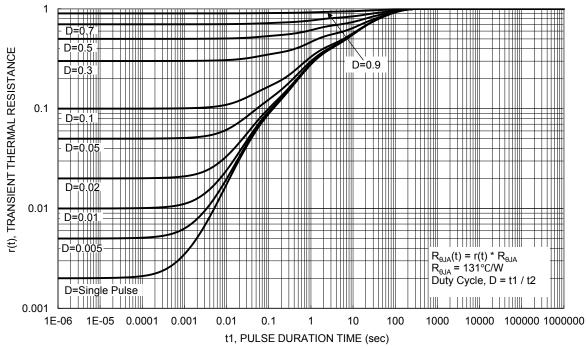


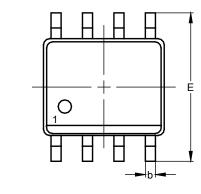
Figure 13. Transient Thermal Resistance

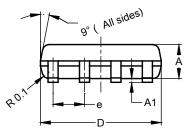


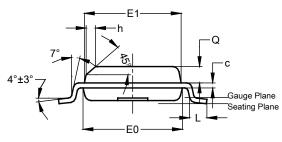
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





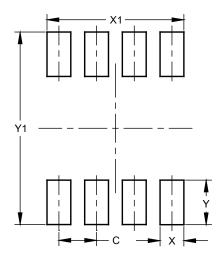


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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